

### Description

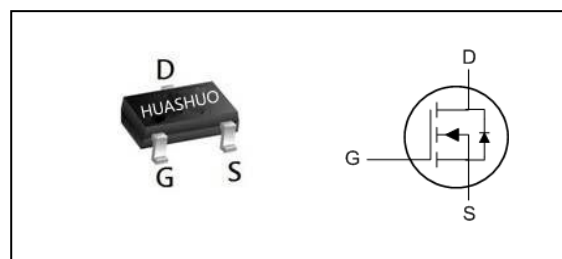
The HSS1N20 is the high cell density trenched N-ch MOSFETs, which provides excellent RDS(ON) and efficiency for most of the small power switching and load switch applications. The HSS1N20 meets the RoHS and Green Product requirement with full function reliability approved.

- Green Device Available
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Advanced high cell density Trench technology

### Product Summary

V <sub>DS</sub>	200	V
R <sub>DS(ON),Max</sub>	1.9	Ω
I <sub>D</sub>	1	A

### SOT-23L Pin Configuration



### Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	200	V
V <sub>GS</sub>	Gate-Source Voltage	±30	V
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sub>1</sub>	1	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sub>1</sub>	0.8	A
I <sub>DM</sub>	Pulsed Drain Current <sub>2</sub>	6	A
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sub>3</sub>	0.71	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

### Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-ambient <sub>1</sub>	---	125	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sub>1</sub>	---	80	°C/W

**N-Ch 200V Fast Switching MOSFETs**
**Electrical Characteristics (T<sub>J</sub>=25 °C, unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
B <sub>VDS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	200	---	---	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance <sup>2</sup>	V <sub>GS</sub> =10V, I <sub>D</sub> =1A	---	1.65	1.9	Ω
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =0.8A	---	1.85	2.2	Ω
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>GS</sub> =V <sub>DS</sub> , I <sub>D</sub> =250uA	1.0	1.7	2.5	V
I <sub>DSS</sub>	Drain-Source Leakage Current	V <sub>DS</sub> =200V, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C	---	---	1	uA
		V <sub>DS</sub> =200V, V <sub>GS</sub> =0V, T <sub>J</sub> =55°C	---	---	5	
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	---	---	±100	nA
g <sub>fs</sub>	Forward Transconductance	V <sub>DS</sub> =15V, I <sub>D</sub> =1A	---	8	---	S
Q <sub>g</sub>	Total Gate Charge (10V)	V <sub>DS</sub> =100V, V <sub>GS</sub> =10V, I <sub>D</sub> =1A	---	12	---	nC
Q <sub>gs</sub>	Gate-Source Charge		---	2.3	---	
Q <sub>gd</sub>	Gate-Drain Charge		---	3.8	---	
T <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> =100V, V <sub>GS</sub> =10V, R <sub>G</sub> =2.5Ω I <sub>D</sub> =1A	---	9	---	ns
T <sub>r</sub>	Rise Time		---	11	---	
T <sub>d(off)</sub>	Turn-Off Delay Time		---	14	---	
T <sub>f</sub>	Fall Time		---	12	---	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1MHz	---	145	---	pF
C <sub>oss</sub>	Output Capacitance		---	88	---	
C <sub>rss</sub>	Reverse Transfer Capacitance		---	3	---	

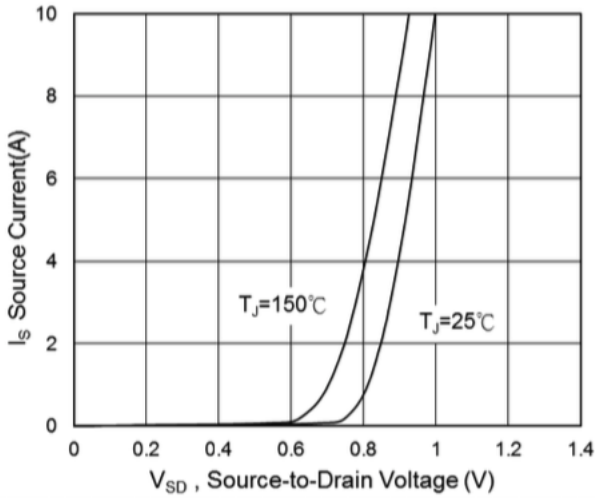
**Diode Characteristics**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I <sub>S</sub>	Continuous Source Current <sup>1,4</sup>	V <sub>G</sub> =V <sub>D</sub> =0V, Force Current	---	---	1	A
V <sub>SD</sub>	Diode Forward Voltage <sup>2</sup>	V <sub>GS</sub> =0V, I <sub>S</sub> =1A, T <sub>J</sub> =25°C	---	---	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> =1A, dI/dt=100A/μs, T <sub>J</sub> =25°C	---	38	---	nS
Q <sub>rr</sub>	Reverse Recovery Charge		---	20	---	nC

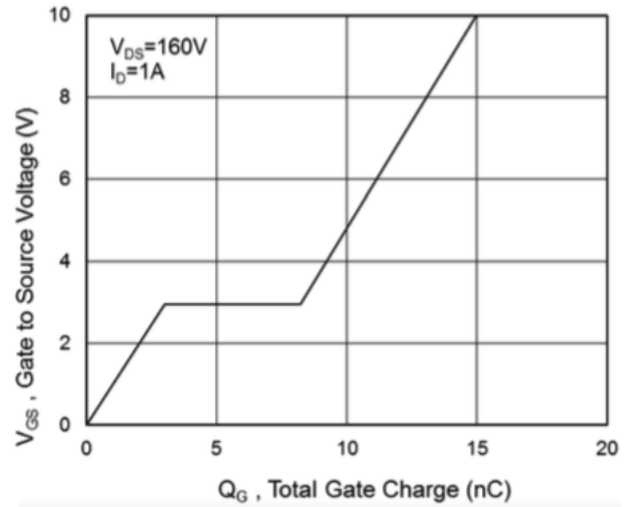
**Note:**

1. The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width ≤ 300us, duty cycle ≤ 2%
3. The power dissipation is limited by 150°C junction temperature
4. The data is theoretically the same as I<sub>D</sub> and I<sub>DM</sub>, in real applications, should be limited by total power dissipation.

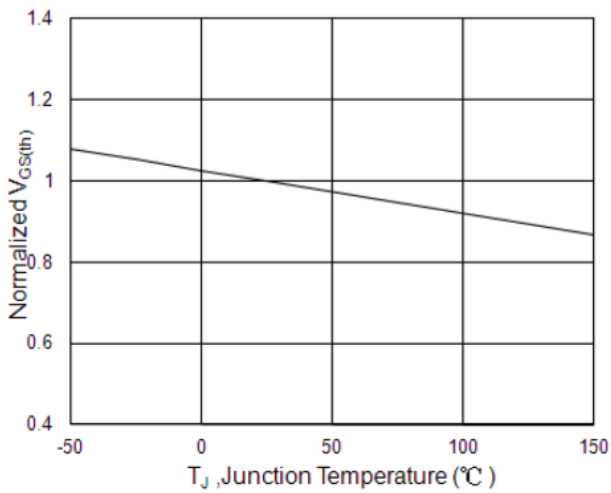
**Typical Characteristics**



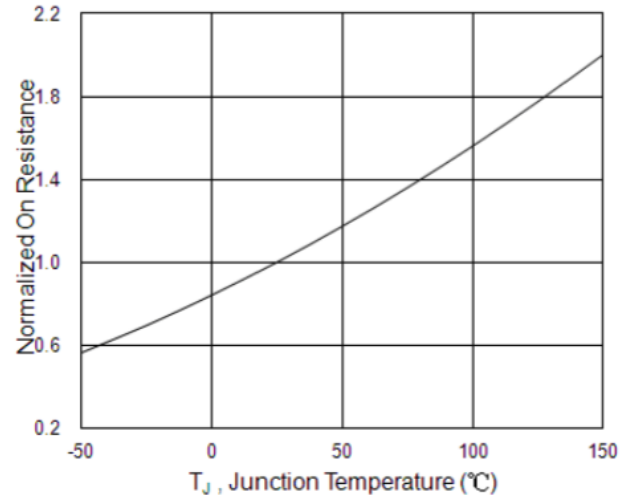
**Fig.1 Forward Characteristics of Reverse**



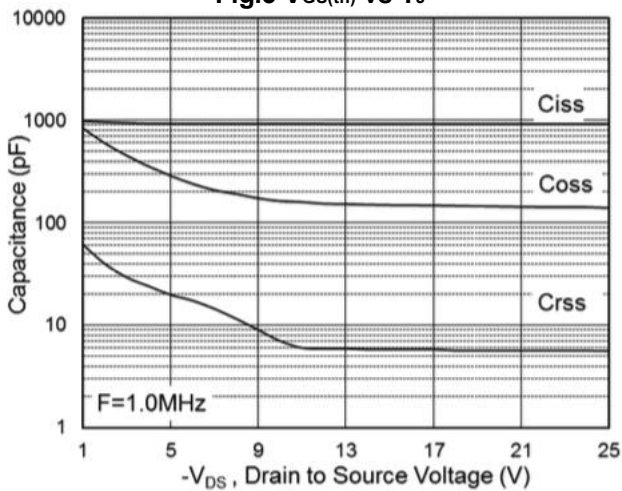
**Fig.2 Gate-Charge Characteristics**



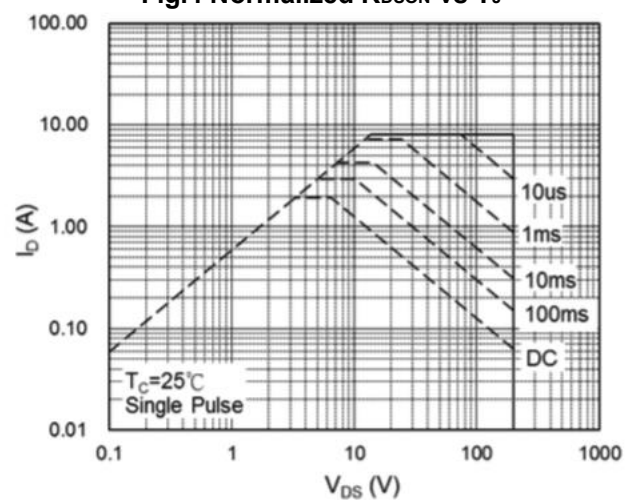
**Fig.3  $V_{GS(th)}$  vs  $T_J$**



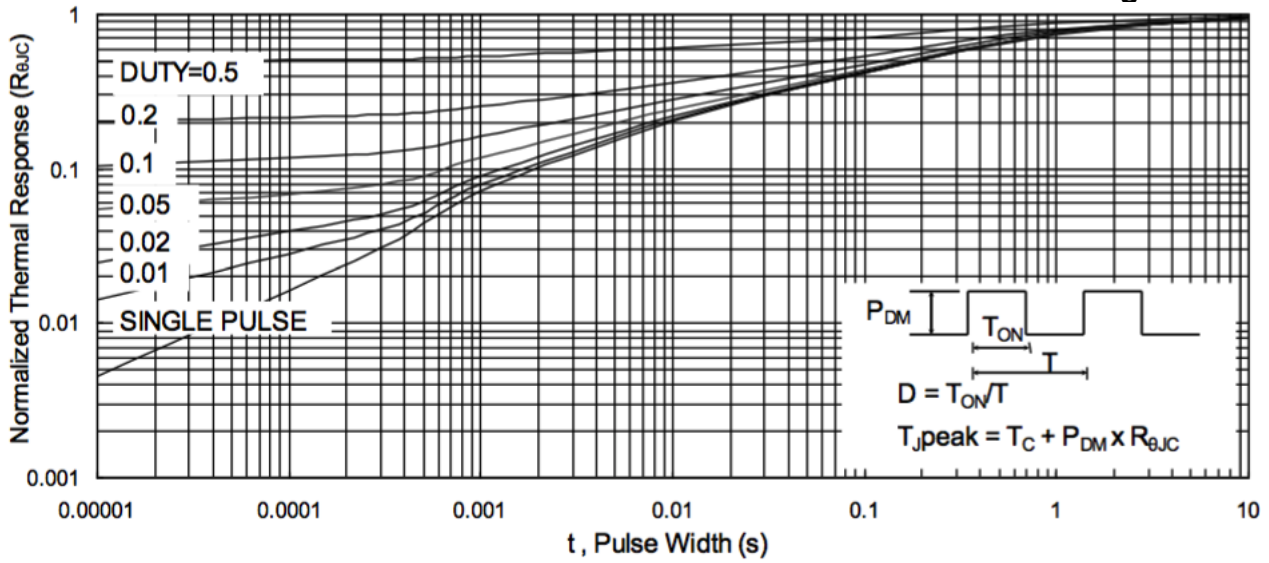
**Fig.4 Normalized  $R_{DS(on)}$  vs  $T_J$**



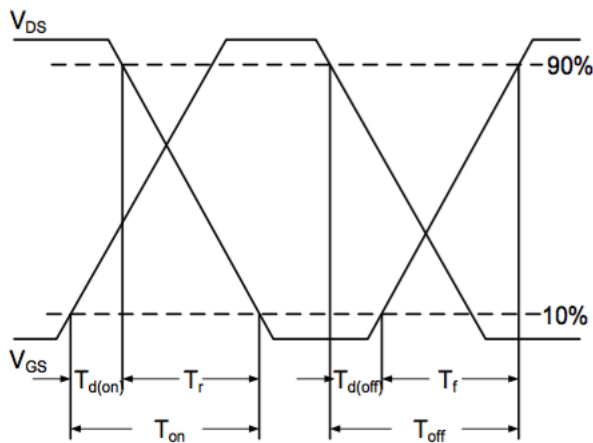
**Fig.5 Capacitance**



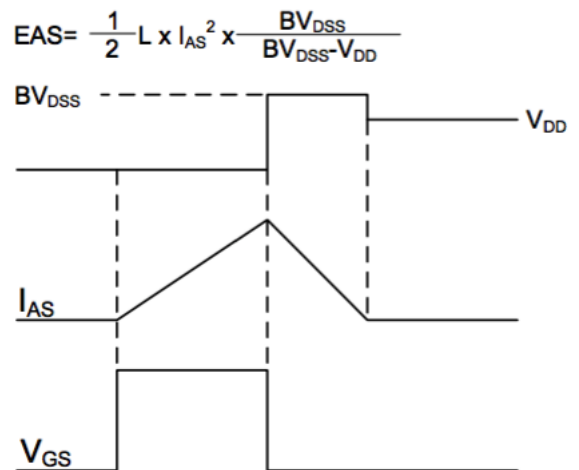
**Fig.6 Safe Operating Area**



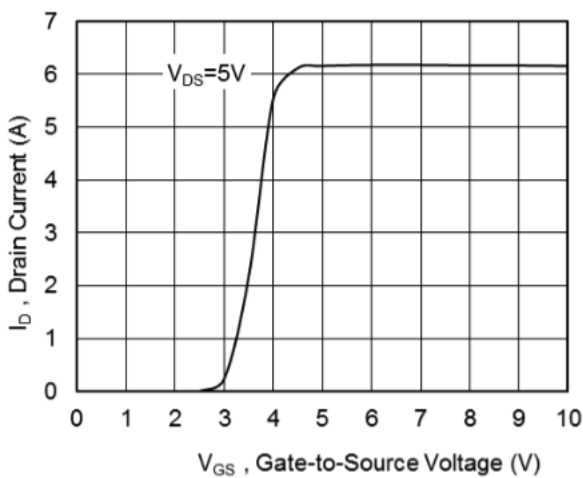
**Fig.7 Normalized Maximum Transient Thermal Impedance**



**Fig.8 Switching Time Waveform**



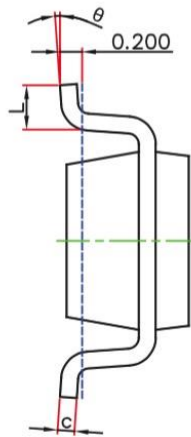
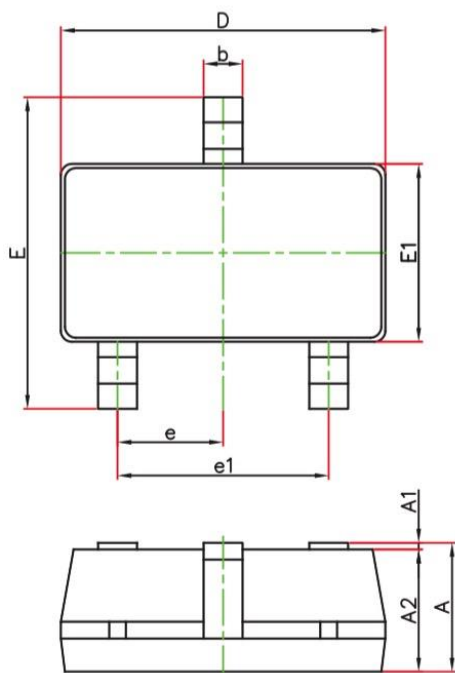
**Fig.9 Gate Charge Waveform**



**Fig.10 Transfer Characteristics**

## Ordering Information

Part Number	Package code	Packaging
HSS1N20	SOT-23L	3000/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°